

# **Ordering Information**

BV <sub>DSS</sub> /	R <sub>DS(ON)</sub>	I <sub>D(ON)</sub>	Order Number / Package Die <sup>†</sup>		
BV <sub>DGS</sub>	(max)	(min)			
40V	3.0Ω	2.0A	VN1504NW		
60V	3.0Ω	2.0A	VN1506NW		
90V	3.0Ω	2.0A	VN1509NW		

<sup>†</sup> MIL visual screening available.

### **Features**

- ☐ Free from secondary breakdown
- Low power drive requirement
- Ease of paralleling
- □ Low C<sub>ISS</sub> and fast switching speeds
- Excellent thermal stability
- ☐ Integral Source-Drain diode
- ☐ High input impedance and high gain
- Complementary N- and P-channel devices

# **Applications**

- Motor controls
- □ Converters
- Amplifiers
- □ Switches
- Power supply circuits
- Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

### **Absolute Maximum Ratings**

Drain-to-Source Voltage	$BV_{DSS}$
Drain-to-Gate Voltage	$BV_{DGS}$
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

<sup>\*</sup> Distance of 1.6 mm from case for 10 seconds.

### **Advanced DMOS Technology**

Thisi enhancement-mode (normally-off) transistori utilizes a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces a device with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, this device is free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

# Electrical Characteristics (@25°C unless otherwise specified)

Symbol	Parameter		Min	Тур	Max	Unit	Conditions
BV <sub>DSS</sub>	Drain-to-Source Breakdown Voltage	VN1504 VN1506 VN1509	40 60 90			V	$V_{GS} = 0V, I_D = 1mA$
V <sub>GS(th)</sub>	Gate Threshold Voltage		0.8		2.4	V	$V_{GS} = V_{DS}, I_D = 1 \text{mA}$
$\Delta V_{GS(th)}$	Change in V <sub>GS(th)</sub> with Temperature			-3.8	-5.5	mV/°C	$V_{GS} = V_{DS}, I_D = 1mA$
I <sub>GSS</sub>	Gate Body Leakage				100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
I <sub>DSS</sub>	Zero Gate Voltage Drain Current				1	μΑ	$V_{GS} = 0V$ , $V_{DS} = Max$ Rating
					100		$V_{GS} = 0V$ , $V_{DS} = 0.8$ Max Rating $T_A = 125$ °C
I <sub>D(ON)</sub>	ON-State Drain Current		0.5	1.0		Α -	$V_{GS} = 5V, V_{DS} = 25V$
			2.0	2.5			$V_{GS} = 10V, V_{DS} = 25V$
R <sub>DS(ON)</sub>	Static Drain-to-Source ON-State Resistance			3.0	5.0	Ω	$V_{GS} = 5V, I_D = 250mA$
				2.5	3.0		V <sub>GS</sub> = 10V, I <sub>D</sub> = 1A
$\Delta R_{DS(ON)}$	Change in R <sub>DS(ON)</sub> with Temperature			0.70	1	%/°C	$V_{GS} = 10V, I_{D} = 1A$
G <sub>FS</sub>	Forward Transconductance		300	450		mΩ	$V_{DS} = 25V, I_{D} = 0.5A$
C <sub>ISS</sub>	Input Capacitance			55	65	pF	$V_{GS} = 0V$ , $V_{DS} = 25V$ f = 1 MHz
C <sub>OSS</sub>	Common Source Output Capacitance			20	25		
C <sub>RSS</sub>	Reverse Transfer Capacitance			5	8		
t <sub>d(ON)</sub>	Turn-ON Delay Time			3	5	ns	$V_{DD} = 25V$ $I_{D} = 1A$ $R_{GEN} = 25\Omega$
t <sub>r</sub>	Rise Time			5	8		
t <sub>d(OFF)</sub>	Turn-OFF Delay Time			6	9		
t <sub>f</sub>	Fall Time			5	8		-GEN -S
V <sub>SD</sub>	Diode Forward Voltage Drop			1.2	1.8	V	$V_{GS} = 0V, I_{SD} = 1.0A$
t <sub>rr</sub>	Reverse Recovery Time			400		ns	V <sub>GS</sub> = 0V, I <sub>SD</sub> =1.0A

### Notes:

- 1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
- 2. All A.C. parameters sample tested.

# Switching Waveforms and Test Circuit

507

**Supertex inc.** does not recommend the use of its products in life support applications, and will not knowingly sell its products for use in such applications, unless it receives an adequate "product liability indemnification insurance agreement". **Supertex** does not assume responsibility for use of devices described and limits its liability to the replacement of the devices determined defective due to workmanship. No responsibility is assumed for possible omissions or inaccuracies. Circuitry and specifications are subject to change without notice. For the latest product specifications, refer to the **Supertex** website: http://www.supertex.com.

NPUT

©2006 **Supertex inc.** All rights reserved. Unauthorized use or reproduction is prohibited.

107

90/



ООТРОТ

٥V